Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- 1 kV ESD protected
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

3. Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| V_{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | - | -5 | Α |
| Static characte | Static characteristics | | | | | | , |
| R _{DSon} | drain-source on-state resistance | V_{GS} = -4.5 V; I_D = -5 A; T_j = 25 °C | | - | 39 | 48 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol | |
|-----|--------|-------------|-----------------------|-----------------|--|
| 1 | D | drain | 1 6 | D I | |
| 2 | D | drain | 7 5 | | |
| 3 | G | gate | | G T | |
| 4 | S | source | 3 8 4 | \ \\ | |
| 5 | D | drain | Transparent top view | | |
| 6 | D | drain | DFN2020MD-6 (SOT1220) | S 017aaa259 | |
| 7 | D | drain | | | |
| 8 | S | source | | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | ackage | | | | | |
|-------------|-------------|---|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| PMPB43XPE | DFN2020MD-6 | DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 | | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMPB43XPE | 1Y |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | V |
| V_{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V_{GS} = -4.5 V; T_{amb} = 25 °C | [1] | - | -5 | Α |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -3.1 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs | | - | -12 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [1] | - | 1.7 | W |
| | | T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 3.5 | W |
| | | T _{sp} = 25 °C | | - | 12.5 | W |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain | diode | | | - | - | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | -1.9 | Α |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

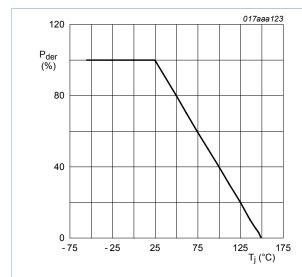


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

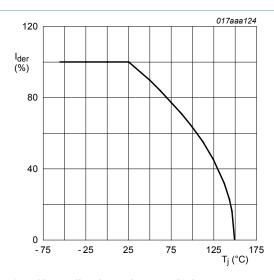


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

PMPB43XPE

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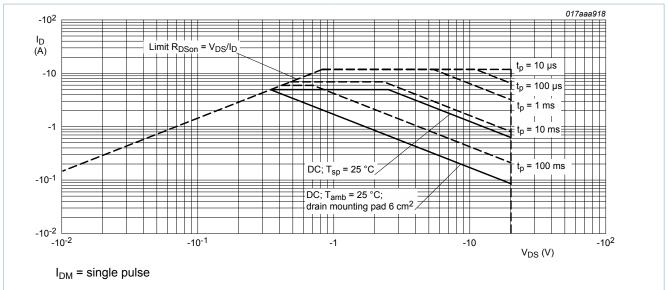


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| fr | thermal resistance | unction to | [1] | - | 235 | 270 | K/W |
| | from junction to ambient | | [2] | - | 67 | 74 | K/W |
| | anibient | in free air; t ≤ 5 s | [2] | - | 33 | 36 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 5 | 10 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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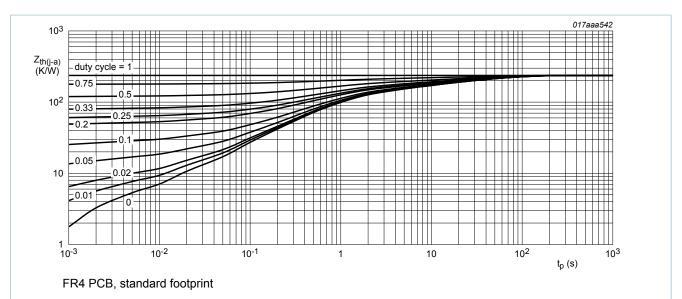


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

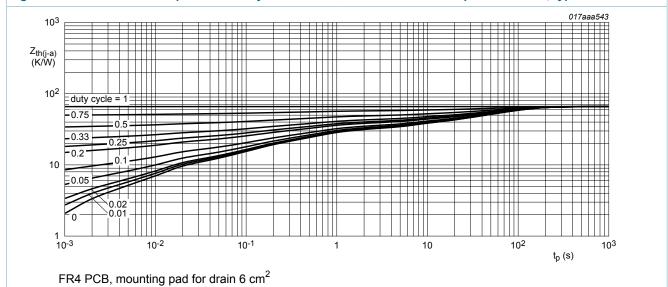


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7 Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--------------------------------|--|-------|-------|------|------|
| Static chara | acteristics | | ' | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | -20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ | -0.47 | -0.68 | -0.9 | V |
| I _{DSS} | drain leakage current | V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C | - | - | -1 | μA |
| I _{GSS} | gate leakage current | V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μA |
| | | V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μA |
| R _{DSon} | drain-source on-state | $V_{GS} = -4.5 \text{ V}; I_D = -5 \text{ A}; T_j = 25 \text{ °C}$ | - | 39 | 48 | mΩ |
| | resistance | V _{GS} = -4.5 V; I _D = -5 A; T _j = 150 °C | - | 55 | 68 | mΩ |
| | | V_{GS} = -2.5 V; I_D = -4.5 A; T_j = 25 °C | - | 45 | 59 | mΩ |
| | | V_{GS} = -1.8 V; I_D = -3.7 A; T_j = 25 °C | - | 56 | 79 | mΩ |
| 9fs | forward transconductance | V_{DS} = -10 V; I_{D} = -5 A; T_{j} = 25 °C | - | 20 | - | S |
| R_G | gate resistance | f = 1 MHz | - | 5.6 | - | Ω |
| Dynamic ch | aracteristics | | ' | | | |
| Q _{G(tot)} | total gate charge | V_{DS} = -10 V; I_{D} = -5 A; V_{GS} = -4.5 V; | - | 15.6 | 23.4 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 1.9 | - | nC |
| Q_{GD} | gate-drain charge | | - | 3.4 | - | nC |
| C _{iss} | input capacitance | V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V; | - | 1550 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 142 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 116 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -10 V; I_{D} = -5 A; V_{GS} = -4.5 V; | - | 9 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 38 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 57 | - | ns |
| t _f | fall time | | - | 25 | - | ns |
| Source-drai | in diode | | ı | - | ' | |
| V_{SD} | source-drain voltage | $I_S = -1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | -0.7 | -1.2 | V |
| | | | | _ | _ | _ |

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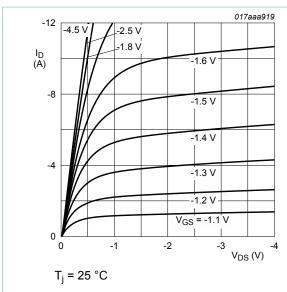


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

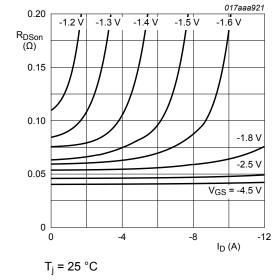


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

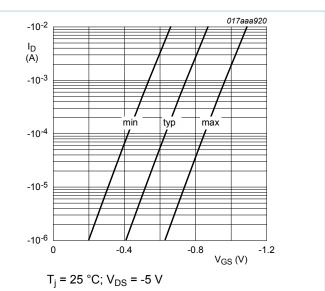


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

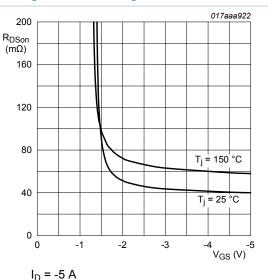


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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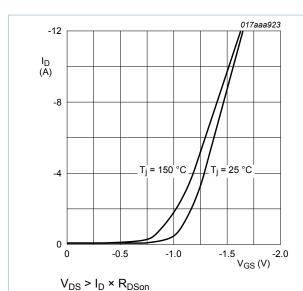


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

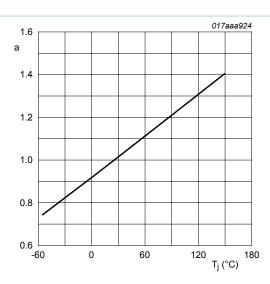


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

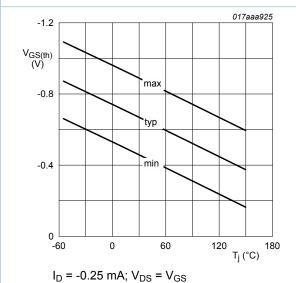


Fig. 12. Gate-source threshold voltage as a function of junction temperature

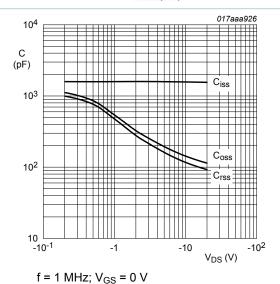


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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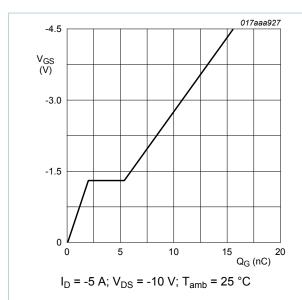


Fig. 14. Gate-source voltage as a function of gate charge; typical values

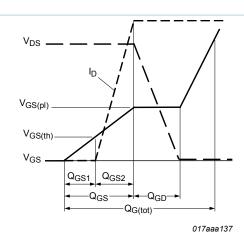


Fig. 15. MOSFET transistor: Gate charge waveform definitions

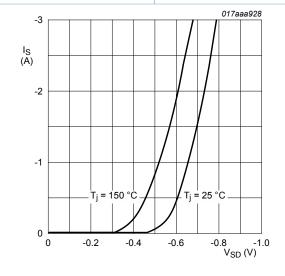
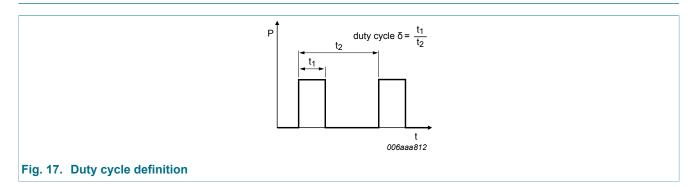


Fig. 16. Source current as a function of source-drain voltage; typical values

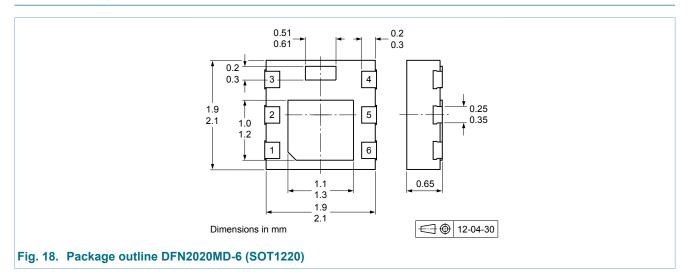
 $V_{GS} = 0 V$

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11. Test information

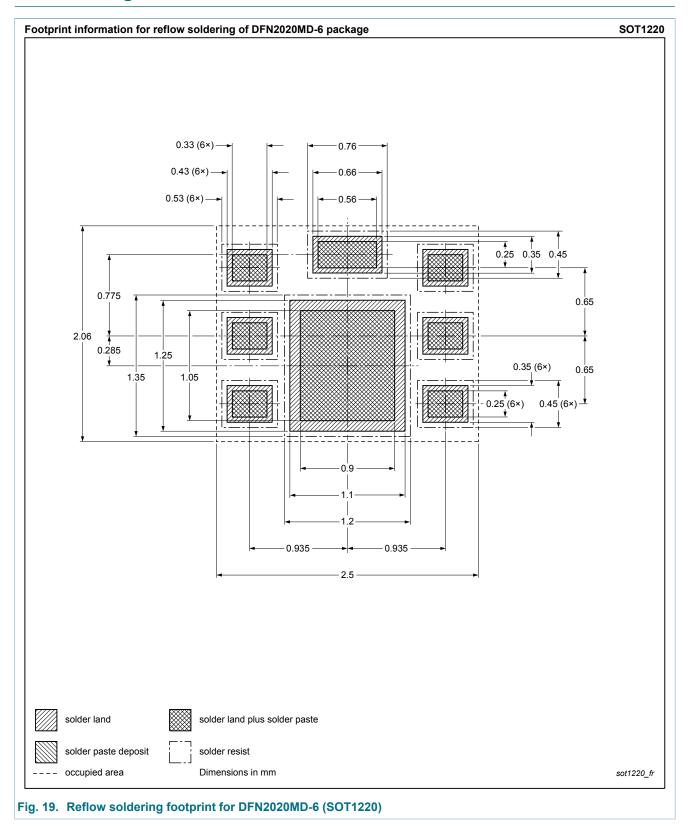


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|---|--------------------|---------------|---------------|
| PMPB43XPE v.2 | 20141126 | Product data sheet | - | PMPB43XPE v.1 |
| Modifications: | 3D package outline Features and benef Table 5: updated | | | |
| PMPB43XPE v.1 | 20121130 | Product data sheet | - | - |

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|--------------------------------------|--------------------|---|
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